

BAT54SWT1G, NSVBAT54SWT1G

Dual Series Schottky Barrier Diodes

These Schottky barrier diodes are designed for high speed switching applications, circuit protection, and voltage clamping. Extremely low forward voltage reduces conduction loss. Miniature surface mount package is excellent for hand held and portable applications where space is limited.

Features

- Extremely Fast Switching Speed
- Low Forward Voltage – 0.35 Volts (Typ) @ $I_F = 10 \text{ mA}$
- NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS ($T_J = 125^\circ\text{C}$ unless otherwise noted)

Rating	Symbol	Value	Unit
Reverse Voltage	V_R	30	V
Forward Power Dissipation @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_F	200 1.6	mW mW/ $^\circ\text{C}$
Forward Current (DC)	I_F	200 Max	mA
Non-Repetitive Peak Forward Current $t_p < 10 \text{ msec}$	I_{FSM}	600	mA
Repetitive Peak Forward Current Pulse Wave = 1 sec, Duty Cycle = 66%	I_{FRM}	300	mA
Junction Temperature	T_J	-55 to 125	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-55 to +150	$^\circ\text{C}$
Electrostatic Discharge	ESD	HM < 8000 MM < 400	V V

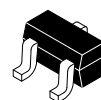
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.



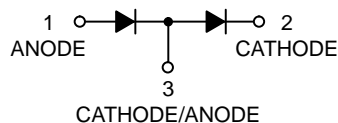
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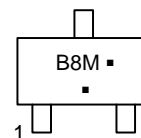
30 VOLT DUAL SERIES SCHOTTKY BARRIER DIODES



SOT-323
CASE 419
STYLE 9



MARKING DIAGRAM



B8 = Device Code
M = Date Code*
▪ = Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping†
BAT54SWT1G	SOT-323 (Pb-Free)	3,000 / Tape & Reel
NSVBAT54SWT1G	SOT-323 (Pb-Free)	3,000 / Tape & Reel

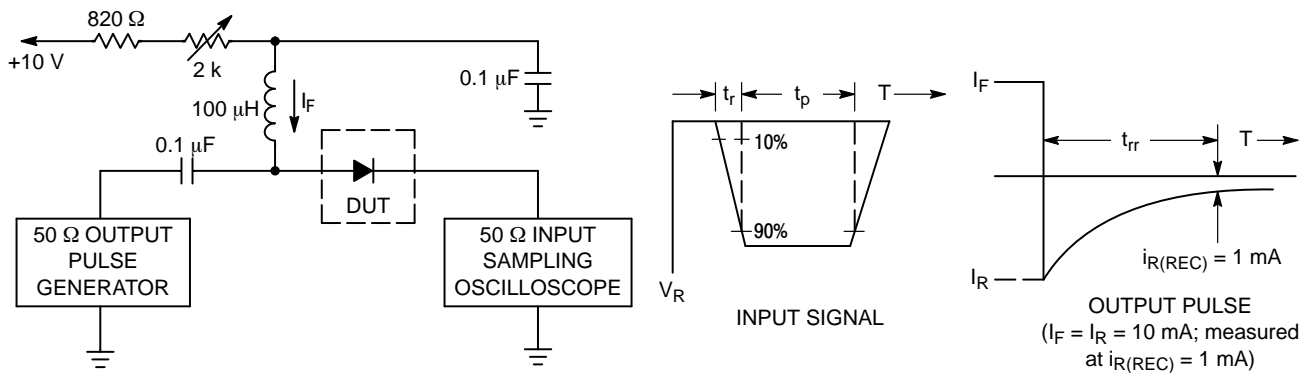
†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted) (EACH DIODE)

Characteristic	Symbol	Min	Typ	Max	Unit
Reverse Breakdown Voltage ($I_R = 10 \mu\text{A}$)	$V_{(BR)R}$	30	-	-	V
Total Capacitance ($V_R = 1.0 \text{ V}$, $f = 1.0 \text{ MHz}$)	C_T	-	7.6	10	pF
Reverse Leakage ($V_R = 25 \text{ V}$)	I_R	-	0.5	2.0	μA_{dc}
Forward Voltage ($I_F = 0.1 \text{ mA}_{dc}$)	V_F	-	0.22	0.24	Vdc
Forward Voltage ($I_F = 30 \text{ mA}_{dc}$)	V_F	-	0.41	0.5	Vdc
Forward Voltage ($I_F = 100 \text{ mA}_{dc}$)	V_F	-	0.52	0.8	Vdc
Reverse Recovery Time ($I_F = I_R = 10 \text{ mA}_{dc}$, $I_{R(REC)} = 1.0 \text{ mA}_{dc}$, Figure 1)	t_{rr}	-	-	5.0	ns
Forward Voltage ($I_F = 1.0 \text{ mA}_{dc}$)	V_F	-	0.29	0.32	Vdc
Forward Voltage ($I_F = 10 \text{ mA}_{dc}$)	V_F	-	0.35	0.40	Vdc

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.



1. A 2.0 kΩ variable resistor adjusted for a Forward Current (I_F) of 10 mA.
2. Input pulse is adjusted so $I_{R(peak)}$ is equal to 10 mA.
3. $t_p \gg t_{rr}$

Figure 1. Recovery Time Equivalent Test Circuit

BAT54SWT1G, NSVBAT54SWT1G

TYPICAL CHARACTERISTICS

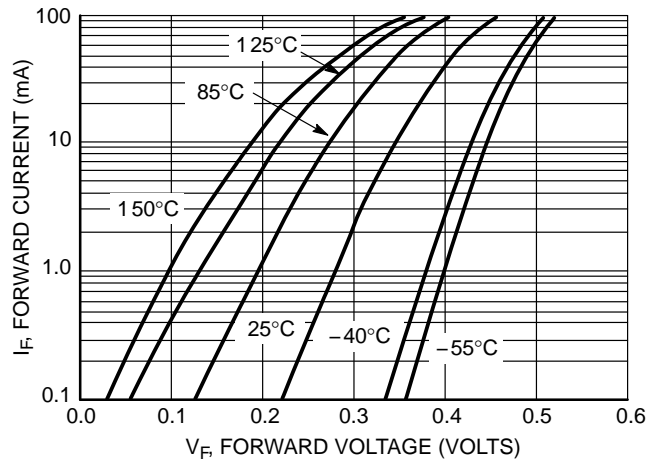


Figure 2. Forward Voltage

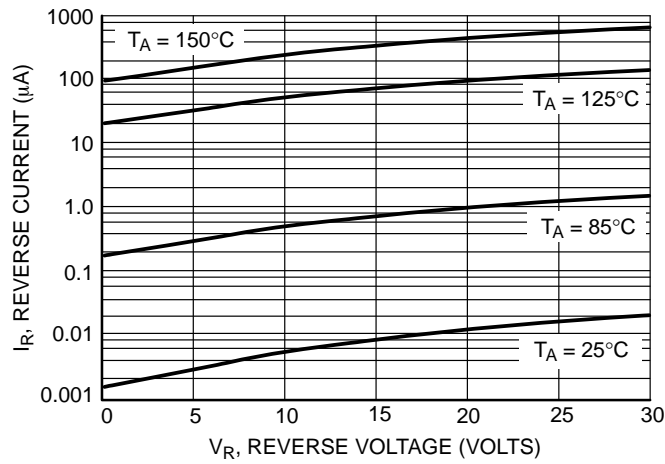


Figure 3. Leakage Current

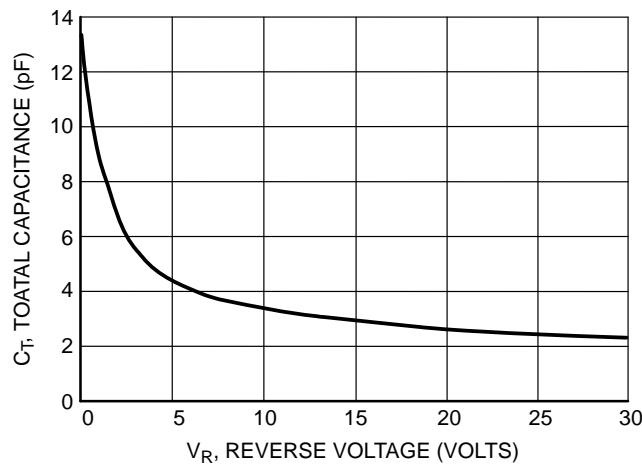
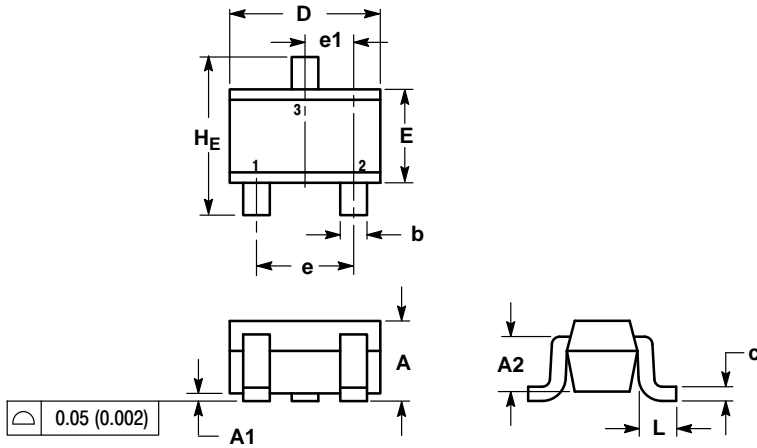


Figure 4. Total Capacitance

BAT54SWT1G, NSVBAT54SWT1G

PACKAGE DIMENSIONS

SOT-323 (SC-70)
CASE 419-04
ISSUE N



NOTES:

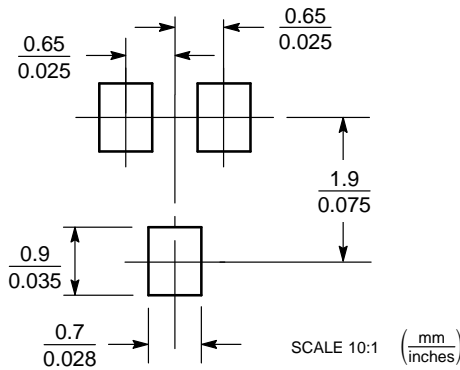
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.80	0.90	1.00	0.032	0.035	0.040
A1	0.00	0.05	0.10	0.000	0.002	0.004
A2	0.70 REF			0.028 REF		
b	0.30	0.35	0.40	0.012	0.014	0.016
c	0.10	0.18	0.25	0.004	0.007	0.010
D	1.80	2.10	2.20	0.071	0.083	0.087
E	1.15	1.24	1.35	0.045	0.049	0.053
e	1.20	1.30	1.40	0.047	0.051	0.055
e1	0.65 BSC			0.026 BSC		
L	0.20	0.38	0.56	0.008	0.015	0.022
HE	2.00	2.10	2.40	0.079	0.083	0.095

STYLE 9:

1. ANODE
2. CATHODE
3. CATHODE-ANODE

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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